



the
abdus salam
international centre for theoretical physics

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ADRIATICO RESEARCH CONFERENCE on
LASERS IN SURFACE SCIENCE

11-15 September 2000

Miramare - Trieste, Italy

*Second harmonic generation from
spherical particles*

W. Luis Mochan Backal
Universidad Nacional Autonoma de Mexico (UNAM)
Cuernavaca, Mexico

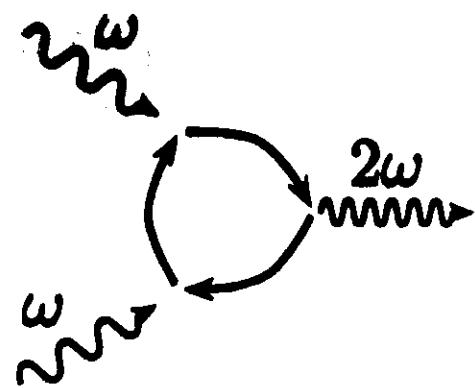
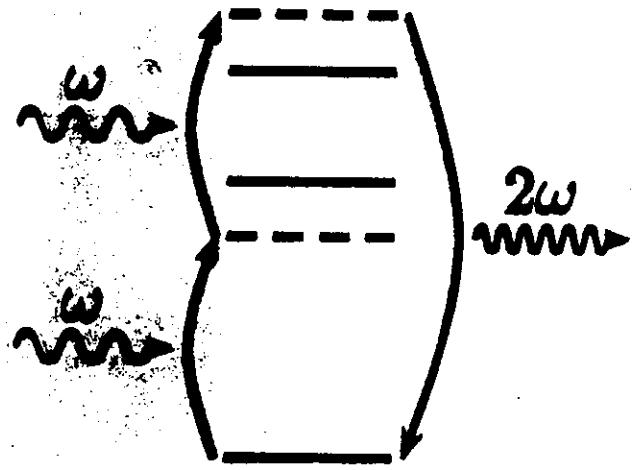
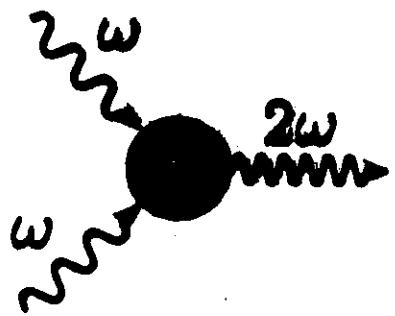
Second harmonic generation from spherical particles

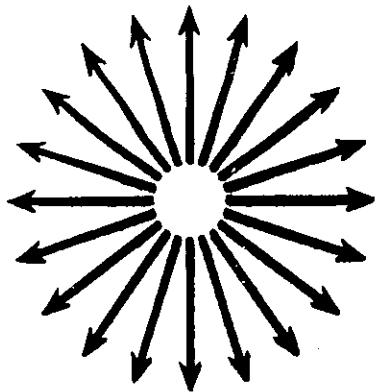
W. Luis Mochán CCF-UNAM

Vera L. Brudny FCEN-UBA, FC-UAEM

Bernardo S. Mendoza CIO

SEIG





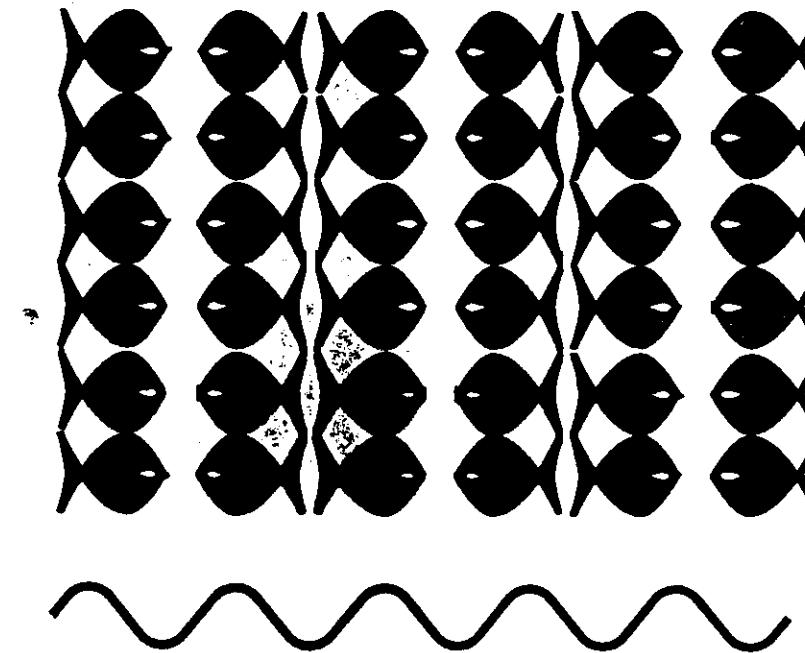
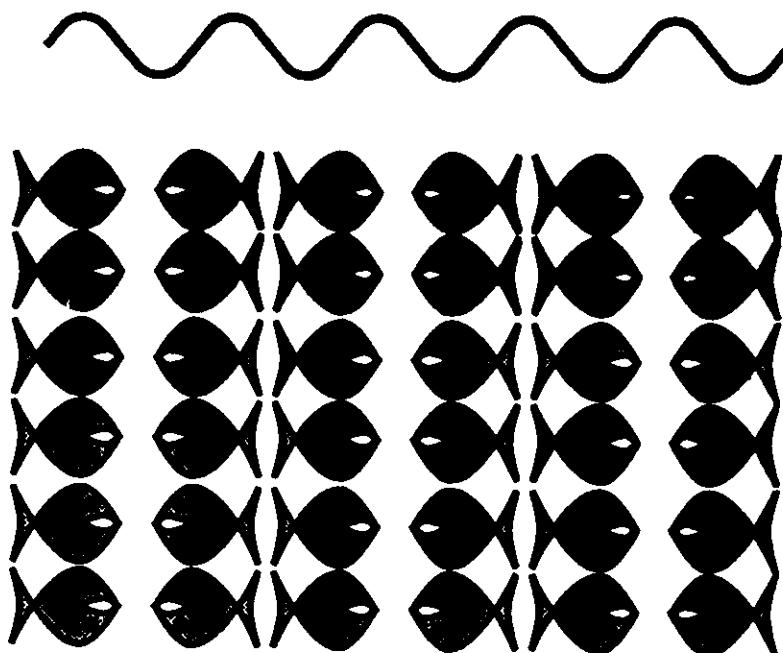
SHG and Symmetry

$$\vec{P}(2\omega) = \chi^{(2\omega)} \vec{E} \vec{E}$$

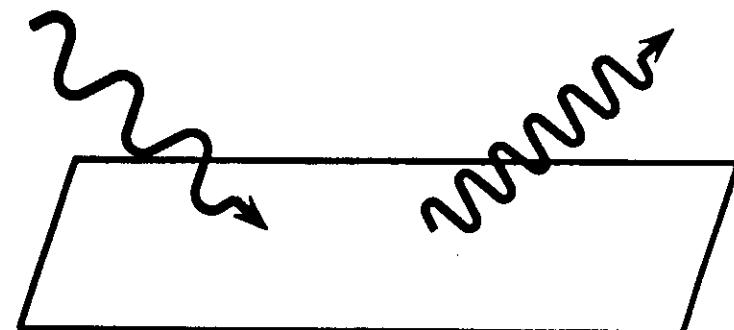
$$(-\vec{P}(2\omega)) = \chi^{(2\omega)} (-\vec{E}) (-\vec{E})$$

Centrosymmetry $\rightarrow \chi^{(2\omega)}$ is invariant
 $\rightarrow \chi^{(2\omega)} = 0$

Surfaces are not

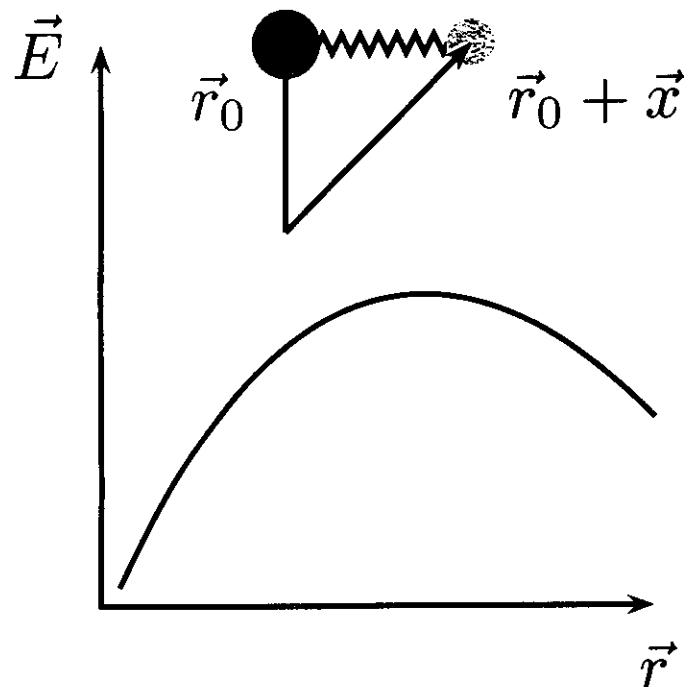


centrosymmetric!



From linear to nonlinear response

Non linear response of harmonic oscillator



$$\vec{F} = -e\vec{E}(\vec{r}_0 + \vec{x})$$

$$m\ddot{\vec{x}} = -m\omega_0^2\vec{x} - e\vec{E}(\vec{r}_0)$$

$$-e\vec{x} \cdot \nabla \vec{E}(\vec{r}_0) - e\frac{\dot{\vec{x}}}{c} \times \vec{B}(\vec{r}_0)$$

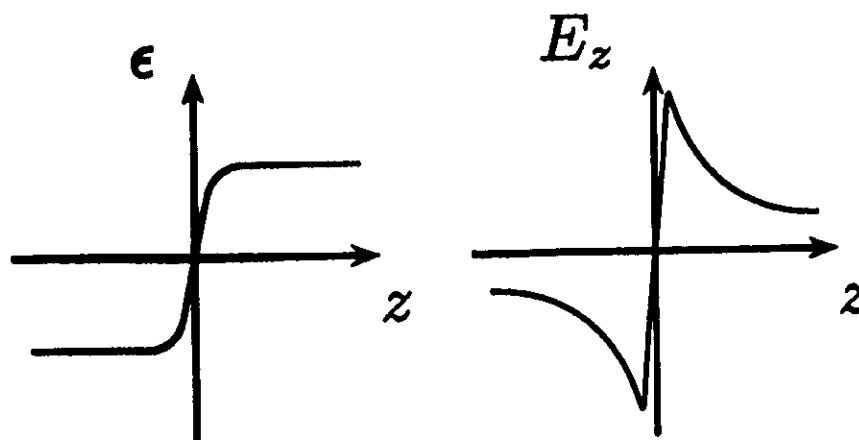
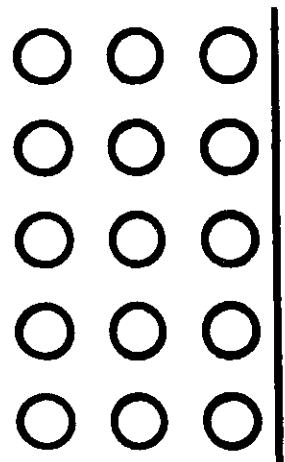
(parametric oscillator)

Dipolium

Single molecule

$$\vec{p}_{2\omega} = -\frac{1}{2e}\alpha(\omega)\alpha(2\omega)\nabla E_\omega^2$$

Solid



B. Mendoza and W.L. Mochán PRB 53 4999 (96)

$$\vec{P}_{2\omega}^i = (\chi_s)^{ijk} E_j E_k$$

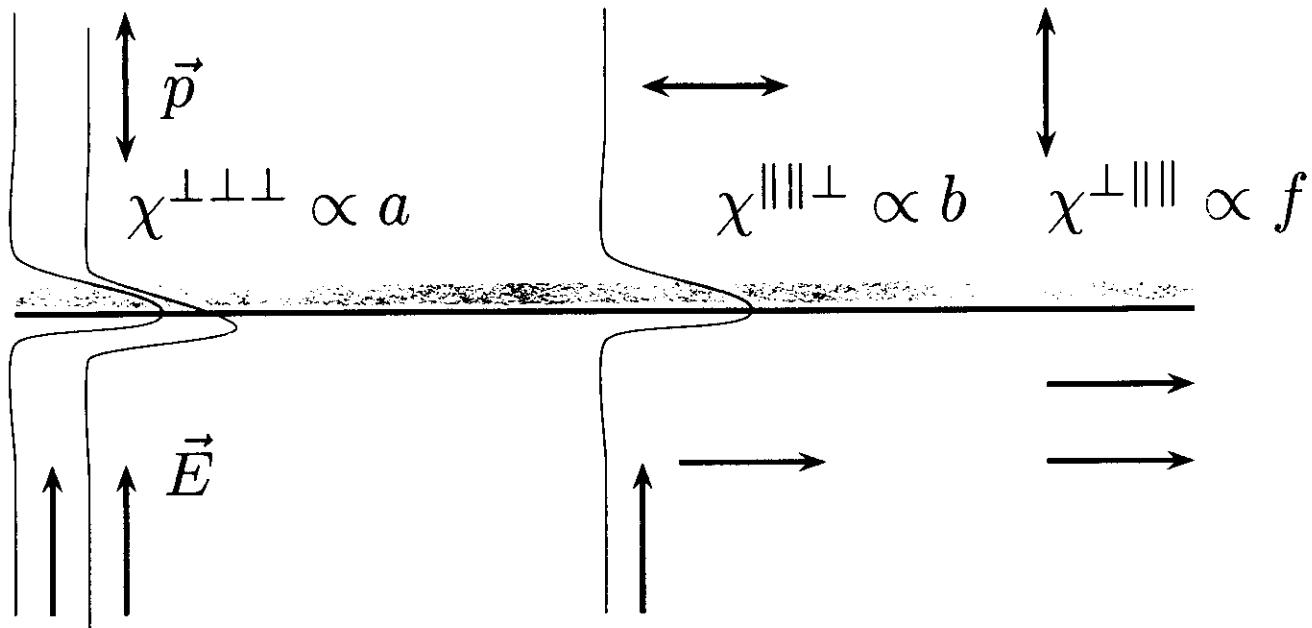
a: $\perp \leftarrow \perp \perp$

b: $\parallel \leftarrow \parallel \perp$

f: $\perp \leftarrow \parallel \parallel$

$$(\chi_s)^{ijk} = (\chi_s)^{ijk}[a, b, f]$$

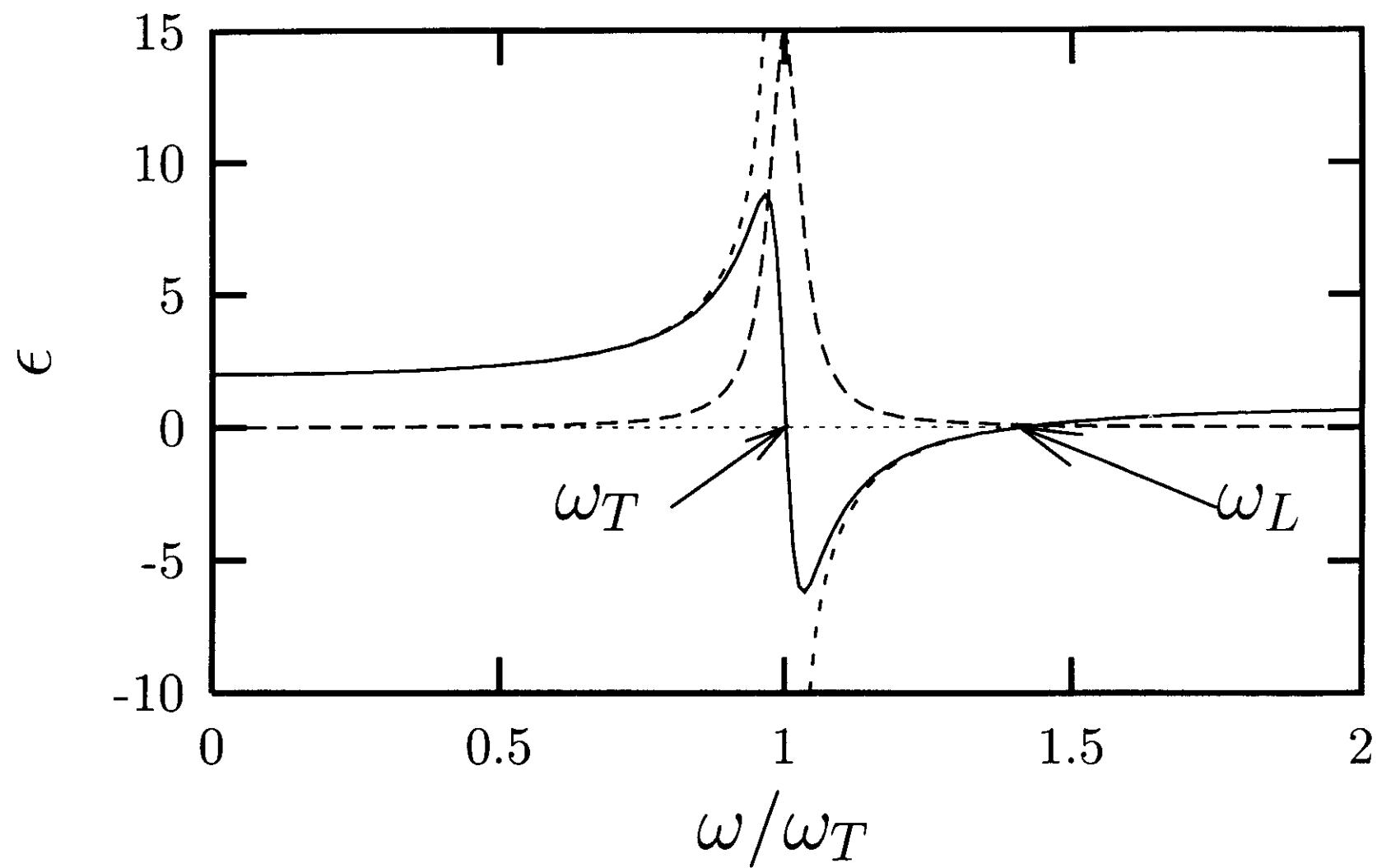
Flat surface



$$p_i = \chi^{ijk} E^i E^k$$

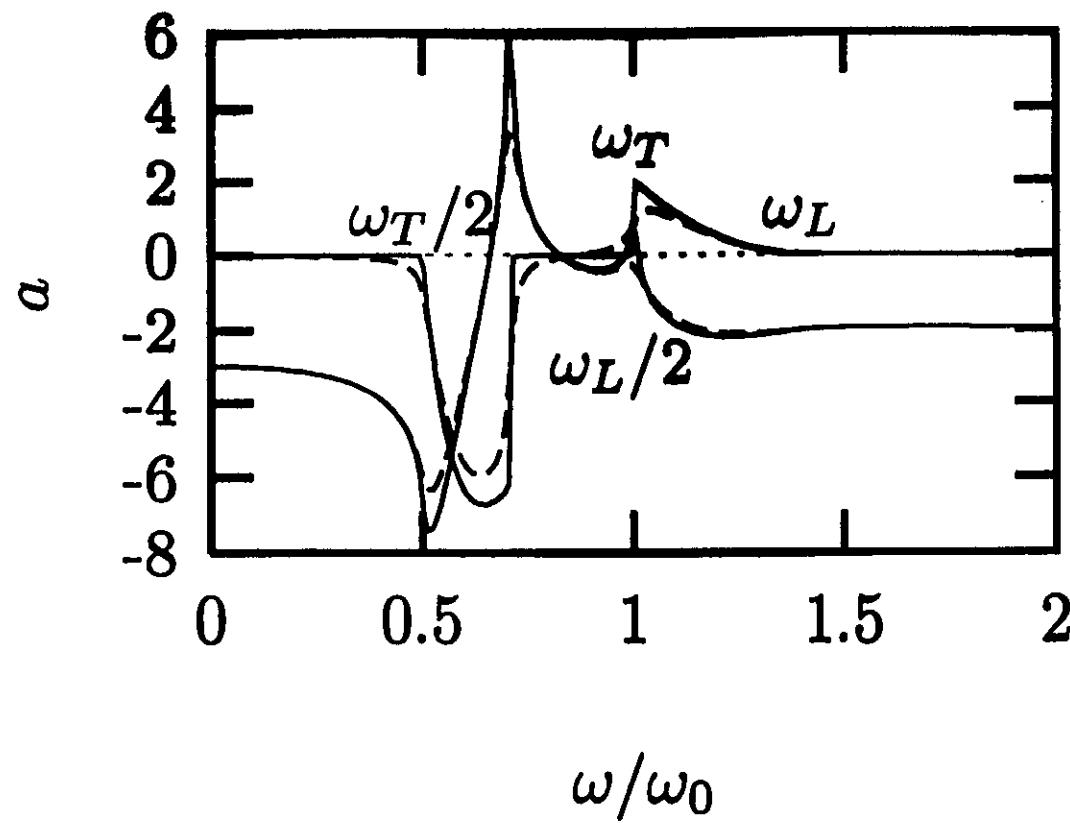
Bulk

$$\vec{p} \propto \nabla E^2, \vec{E} \times \vec{B}$$



$$\epsilon = \frac{\omega_L^2 - \omega^2 - i\omega/\tau}{\omega_T^2 - \omega^2 - i\omega/\tau}$$

$$\omega_p = \omega_0, \omega_0\tau = 1000, 20, \omega_L = \sqrt{2}\omega_0$$



Applications:

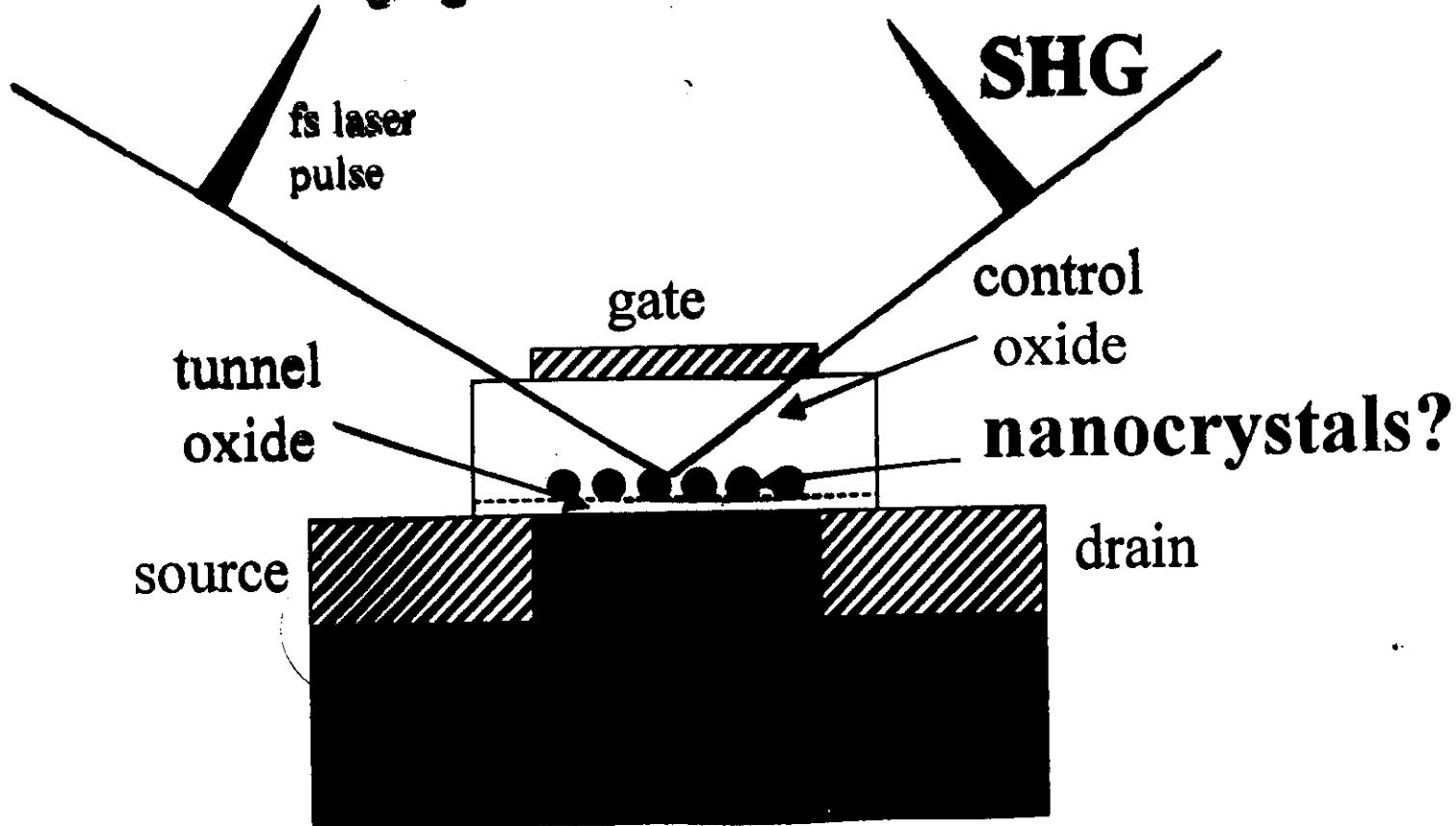
SHG+SFG+DFG,
semiconductors and metals,
continuous + crystalline,
truncated bulk + surface relaxation,
clean + adsorbate covered,
interband + intraband + collective excitations,
magnetism + chirality,

...

Next:



Nanocrystal technology promises novel device that are challenging to fabricate and characterize



From Tiwari et al., "A silicon nanocrystal based memory", APL 1996

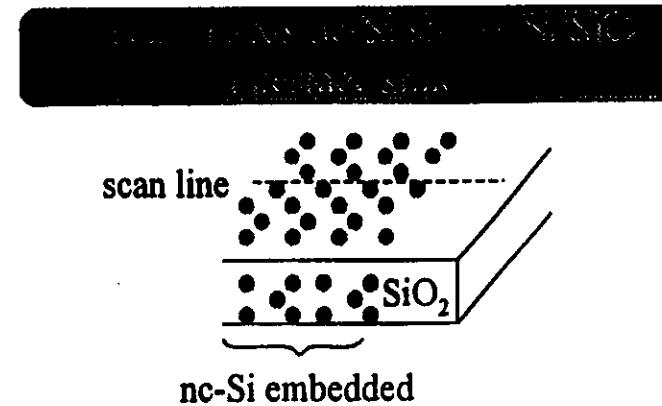
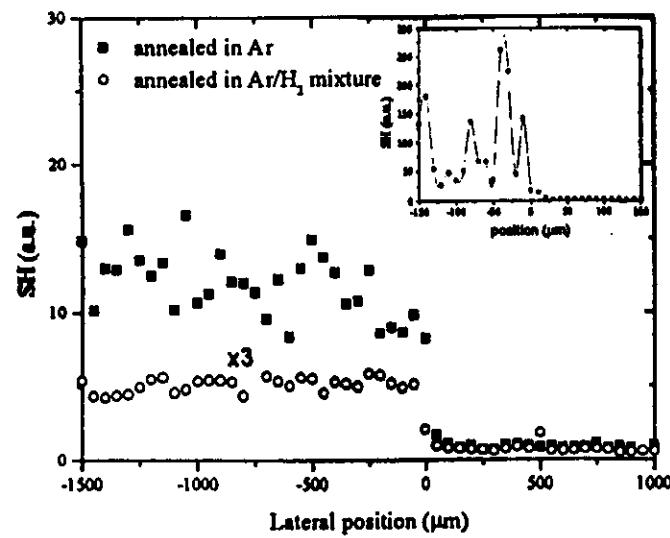
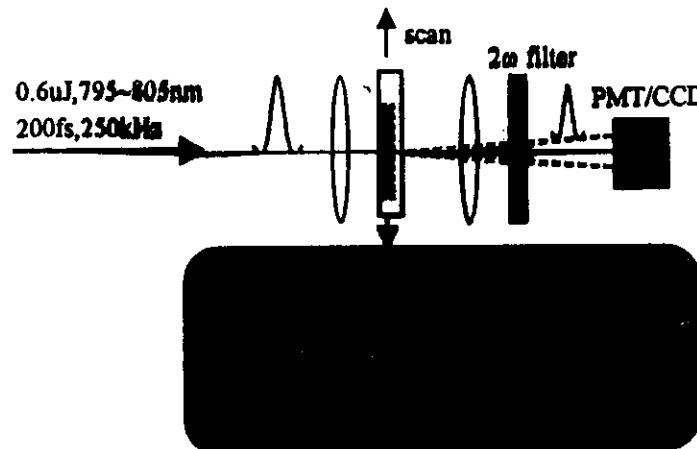
stolen from M. Downer

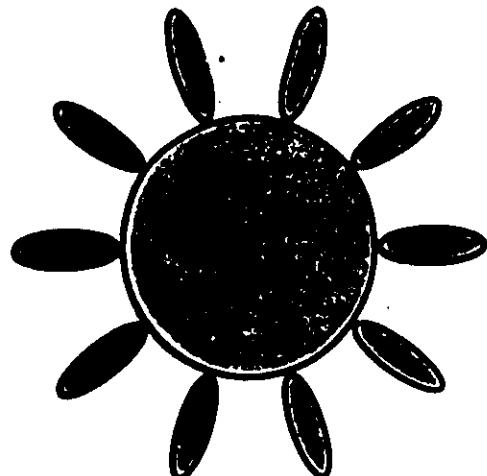
30 - 80 nm

17.08.2007

Transmitted SHG from Si nanocrystals in glass

- experimental setup and scan signal

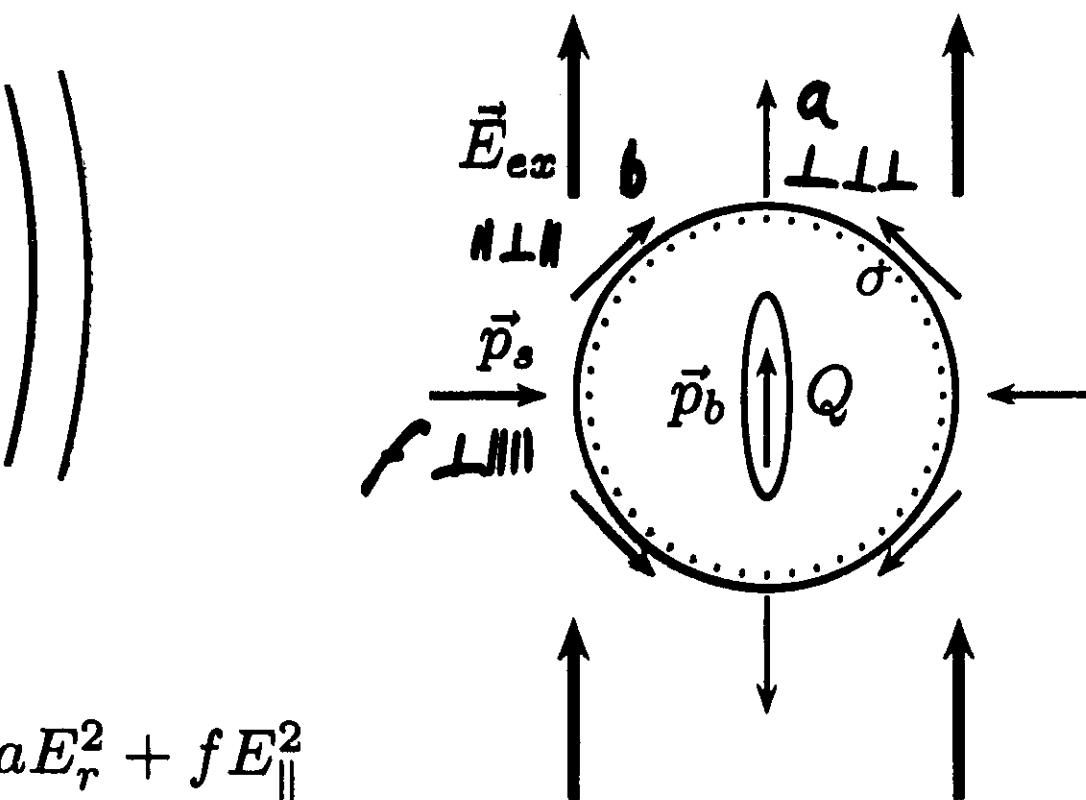




Sphere

- Östling et al, Z. Phys., D **28**, 169 (93).
- Aktsipetrov et al, Surf. Sci. **325**, 343 (95).
- Wang et al, Chem. Phys. Lett. **259**, 15 (96).
- Antoine et al, J. Appl Phys. **84**, 4532 (98).
- Dadap et al, Phys. Rev. Lett. , (99).
 - M. Downer
 - T. Heinz

Locally flat sphere



\vec{E} homogeneous
 $\Rightarrow \vec{p} = 0$

$$P_r \propto a E_r^2 + f E_{\parallel}^2$$

$$P_{\parallel} \propto b E_r E_{\parallel}$$

Phenomenology

\vec{E} homogeneous $\Rightarrow \vec{p} = 0$.

Then, $\vec{p} \approx \vec{E}, \vec{E}, \nabla, \nabla^2, \dots$

$$\vec{p} = \gamma^d \vec{E} \cdot \nabla \vec{E} + \dots \vec{E} \nabla \cdot \vec{E} + \dots \nabla \vec{E} \cdot \vec{E}$$

$$Q^{ij} = \gamma^Q \left(E^i E^j - \frac{1}{3} E^2 \delta^{ij} \right)$$

$$\gamma^d(\omega) = ? \quad \gamma^Q(\omega) = ?$$

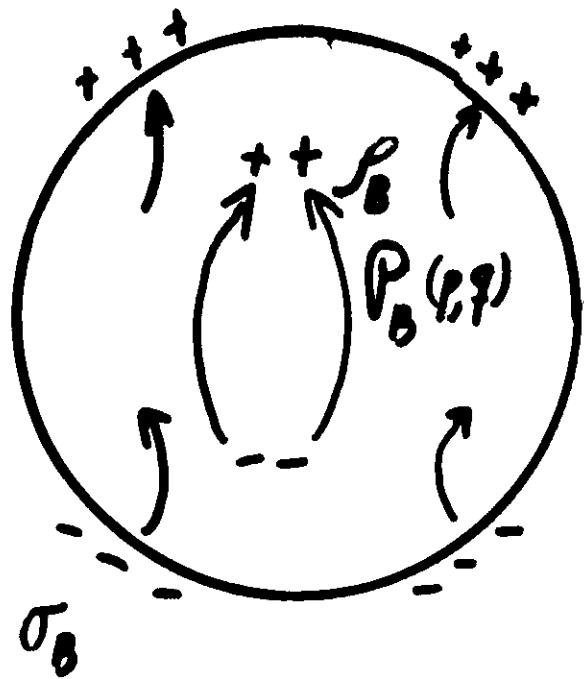
Inhomogeneous field

$$\phi^{\text{ex}} = A_{10}rY_{10} + A_{20}r^2Y_{20}.$$

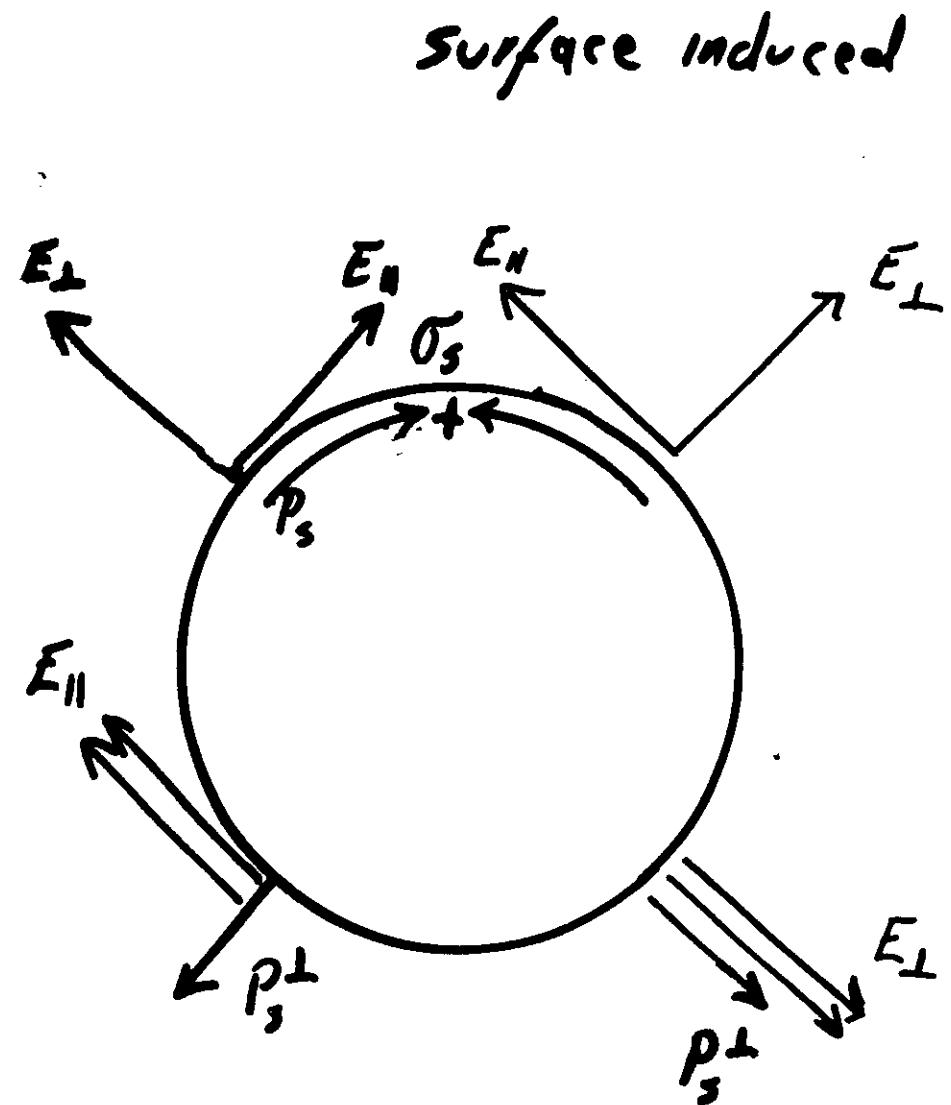
Linear screening

$$\phi_1 = \begin{cases} A_{10} \left(1 - \frac{\epsilon_1 - 1}{\epsilon_1 + 2} \left(\frac{R}{r} \right)^3 \right) r Y_{10} \\ \quad + A_{20} \left(1 - 2 \frac{\epsilon_1 - 1}{2\epsilon_1 + 3} \left(\frac{R}{r} \right)^5 \right) r^2 Y_{20}, & r > R, \\ A_{10} \frac{3}{\epsilon_1 + 2} r Y_{10} + A_{20} \frac{5}{2\epsilon_1 + 3} r^2 Y_{20}, & r < R, \end{cases}$$

Sources



Bulk induced



Surface induced

$$\vec{P}^{\rm nl}=n\vec{p}^{\rm nl}-\frac{1}{2}n\nabla\cdot q^{\rm nl}$$

$$\vec{p}^{\rm nl}=-\frac{1}{2e}\alpha_1\alpha_2\nabla E_1^2$$

$$q^{\rm nl}=-\frac{1}{e}\alpha_1^2\vec{E}_1\vec{E}_1$$

$$\rho^{\rm nl}=-\nabla\cdot\vec{P}^{\rm nl}=-\frac{375n}{4\pi e}\frac{\alpha_1(\alpha_1-2\alpha_2)}{(3+2\epsilon_1)^2}A_{20}^2\propto|\nabla\vec{E}^{\rm ex}|^2$$

$$\begin{array}{lcl} \sigma^{{\rm nl}\, b} & = & \vec{P}^{\rm nl}(R^-)\cdot\hat{r}\\ \\ & = & \dfrac{5n}{16\pi e}\alpha_1(\alpha_1-2\alpha_2)\left(\dfrac{12\sqrt{15}\cos\theta}{(\epsilon+2)(2\epsilon+3)}A_{10}A_{20}\right)+\dots\end{array}$$

$$\begin{aligned}
\sigma^s &= -\nabla_{\parallel} \cdot \vec{P}_{\parallel}^s \\
&= \frac{3(\epsilon_1 - 1)^2 b}{256 n e \pi^3 R} \left(9 \frac{(1 + 3 \cos 2\theta)}{(\epsilon_1 + 2)^2} A_{10}^2 \right. \\
&\quad \left. + 20 \sqrt{15} R \frac{2 \cos \theta + 3 \cos 3\theta}{(\epsilon_1 + 2)(2\epsilon_1 + 3)} A_{10} A_{20} + \dots \right)
\end{aligned}$$

$$\begin{aligned}
P_{\perp}^s &= \frac{(\epsilon_1 - 1)^2}{256 n e \pi^3} \left(27 \frac{a \cos^2 \theta + f \sin^2 \theta}{(\epsilon_1 + 2)^2} A_{10}^2 \right. \\
&\quad \left. + 15 \sqrt{15} R \cos \theta \frac{4a + 6(f - a) \sin^2 \theta}{(\epsilon_1 + 2)(2\epsilon_1 + 3)} A_{10} A_{20} + \dots \right).
\end{aligned}$$

Non linear field eqs.

$$\phi_2 = \phi^b + \phi^s,$$

ϕ^b has bulk sources, not yet screened, while ϕ^s has surface sources, already screened.

$$\nabla^2 \phi^b = -4\pi \rho^{\text{nl}} / \epsilon_2 \text{ (inside), } 0 \text{ (outside)}$$

$$\nabla^2 \phi^s = 0 \text{ (inside and outside)}$$

Boundary conditions

$$\phi^b(R^+) - \phi^b(R^-) = 0,$$

$$\phi^s(R^+) - \phi^s(R^-) = 4\pi P_\perp^s,$$

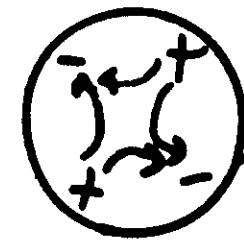
$$\frac{\partial}{\partial R} \phi^b(R^+) - \epsilon_2 \frac{\partial}{\partial R} \phi^b(R^-) = -4\pi \sigma^b,$$

$$\frac{\partial}{\partial R} \phi^s(R^+) - \frac{\partial}{\partial R} \phi^s(R^-) = -4\pi \sigma^s.$$

Solution

$$\phi_{l0}^\lambda = \begin{cases} F_{l0}^\lambda r^l, & (\text{inside}) \\ \frac{4\pi}{2l+1} \frac{q_{l0}^\lambda}{r^{l+1}}, & (\text{outside}) \end{cases}$$

$q_{l0}^\lambda = q_{l0}^\lambda(\rho^{\text{nl}}, \sigma^{\text{nl } b}, \sigma^s, P_\perp^s)$ = (spherical) multipoles
 $\implies \gamma^d, \gamma^Q$



Hyperpolarizabilities

$$\gamma^d = \frac{1}{8\pi n e} \frac{\epsilon_1 - 1}{(\epsilon_1 + 2)(2\epsilon_1 + 3)} \left(15 \frac{\epsilon_1 - 2\epsilon_2 + 1}{\epsilon_2 + 2} + (\epsilon_1 - 1)(2a + b + 3f) \right) \underline{R}^3,$$

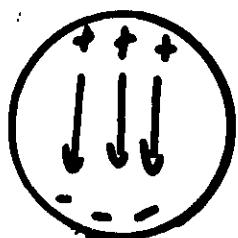
← β
 ← D'

D

Q

$$\gamma^Q = \frac{9}{20\pi n e} \frac{(\epsilon_1 - 1)^2}{(\epsilon_1 + 2)^2} (a + 3b - f) \underline{R}^3.$$

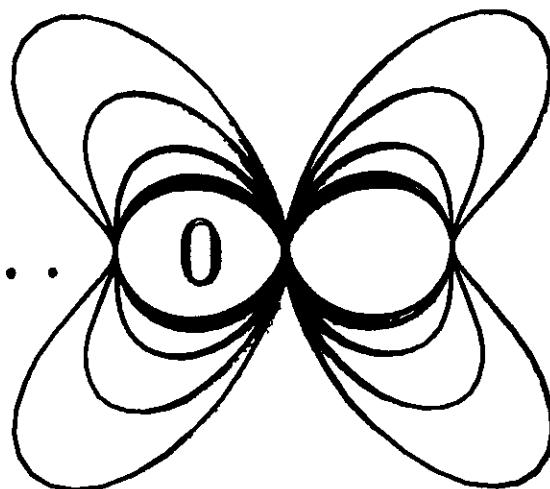
← ς



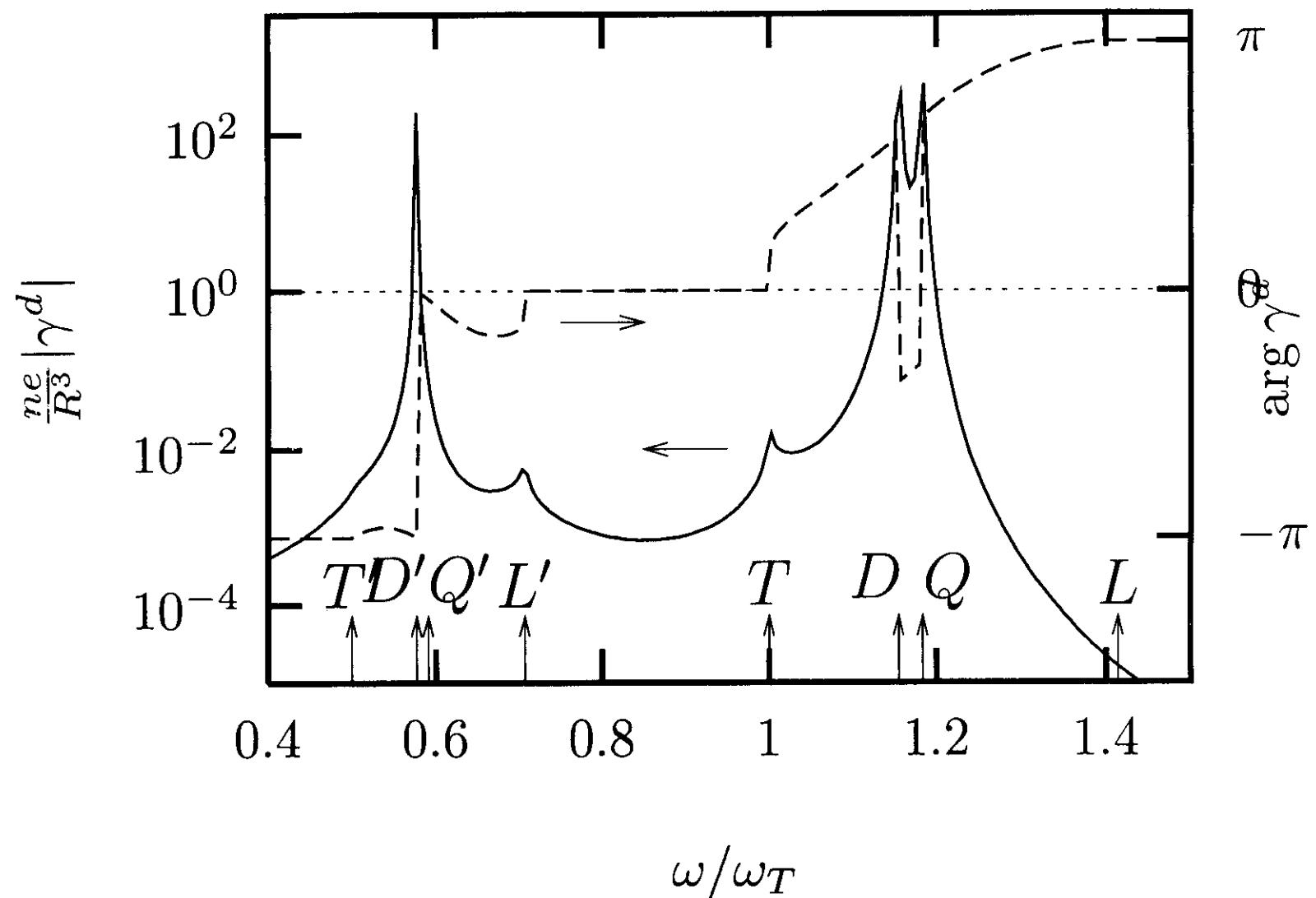
$$\epsilon_1 = \epsilon_2 = 2, a = -2, b = -1, f = 0$$

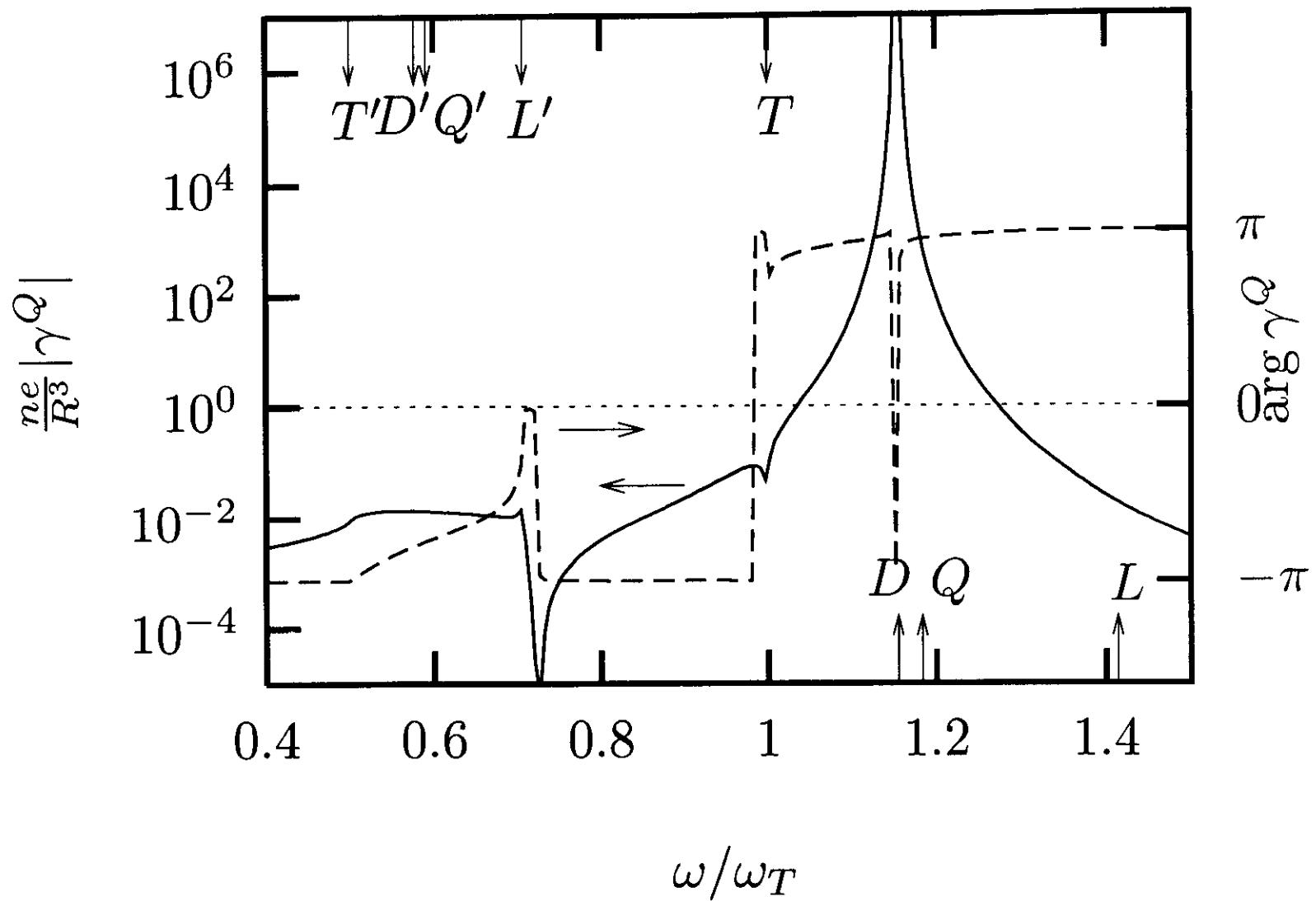
$$\frac{d\sigma}{d\Omega} \text{ vs. } \theta$$

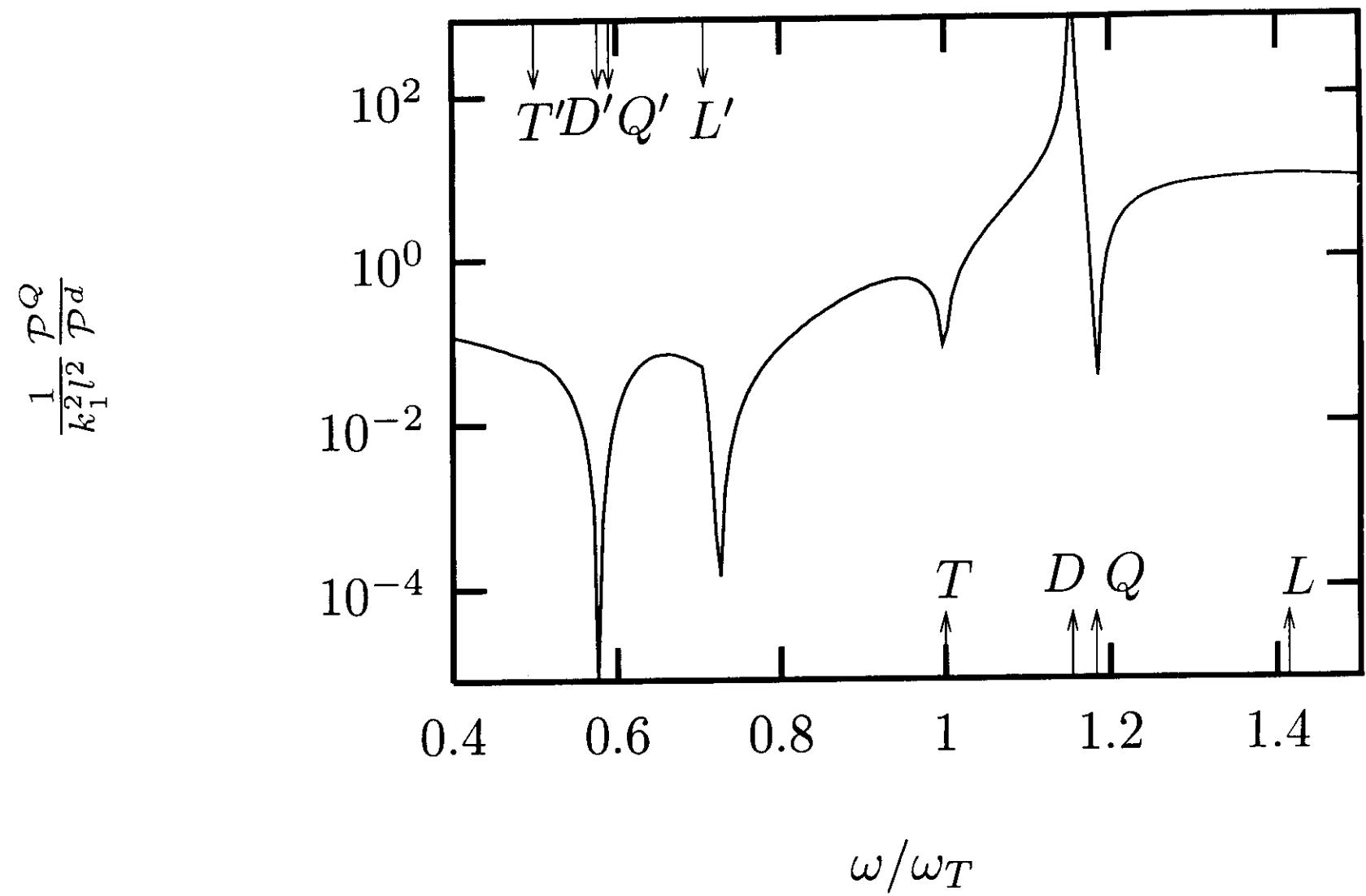
$$k_1 l = 2 \dots 0$$



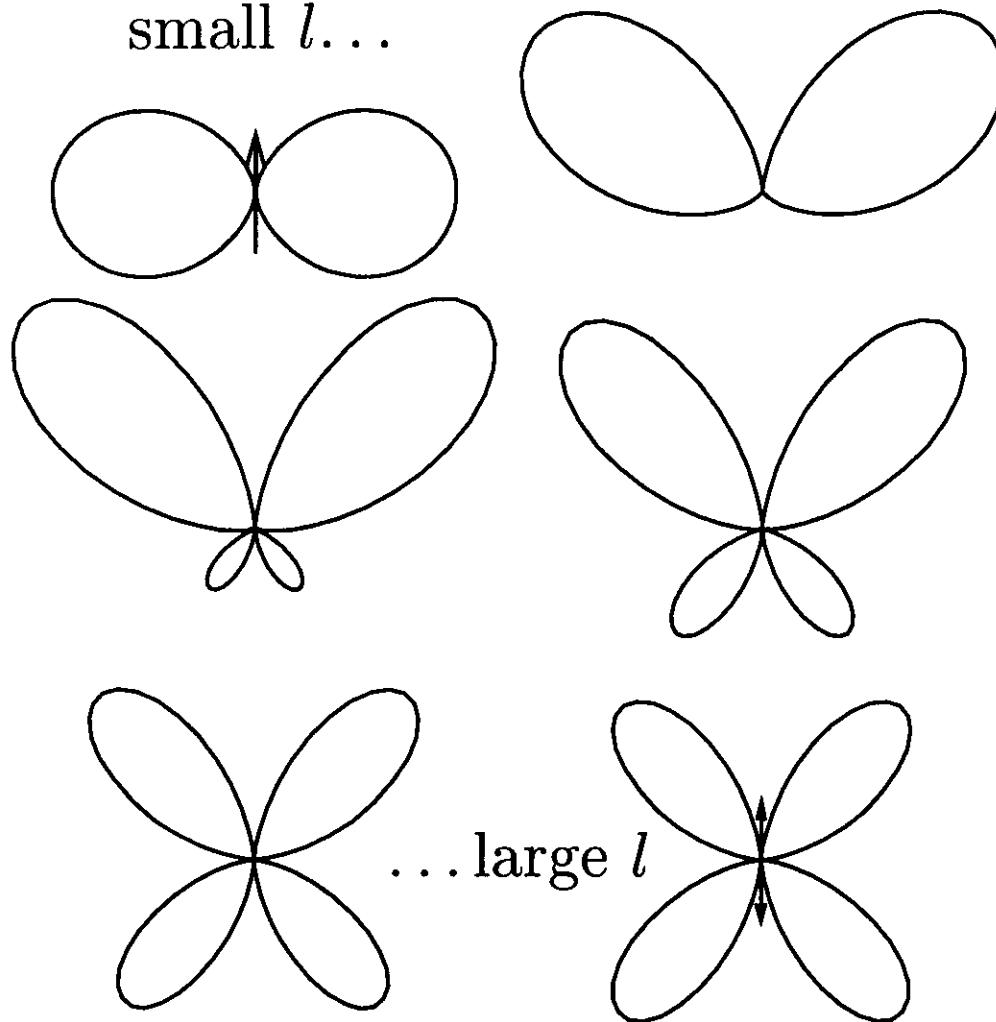
$$\ell = |E/\Delta E|$$



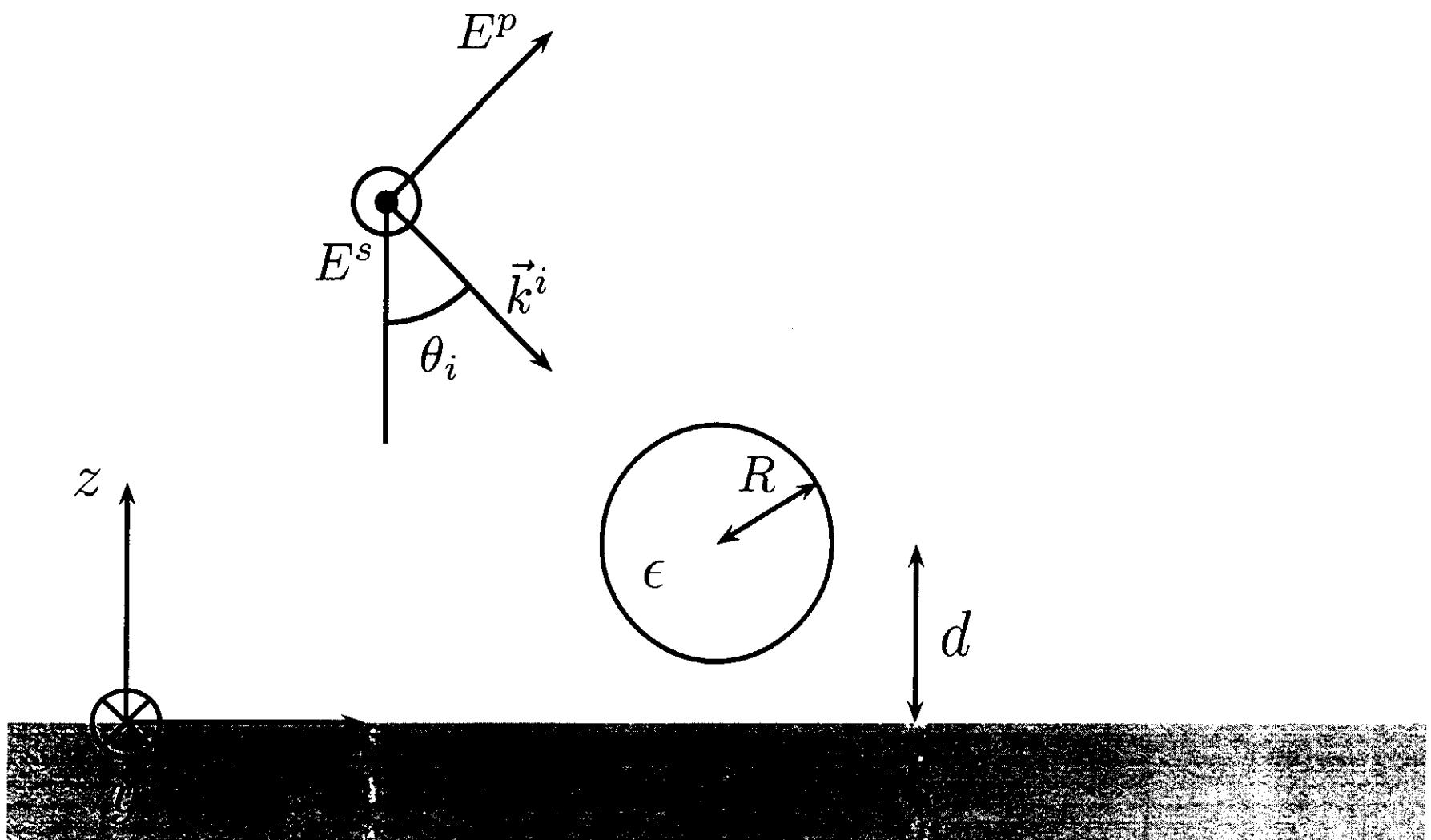


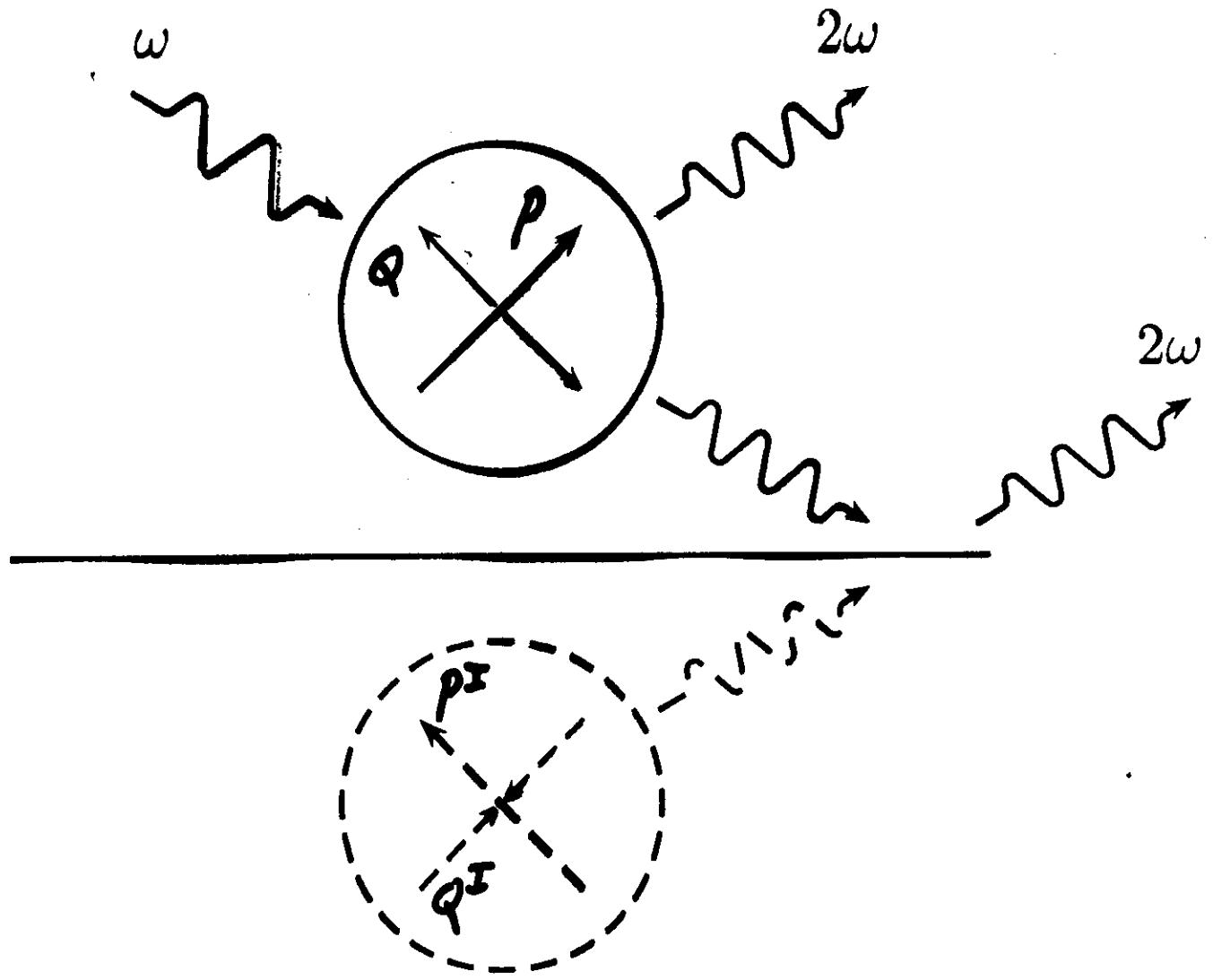


small l ...

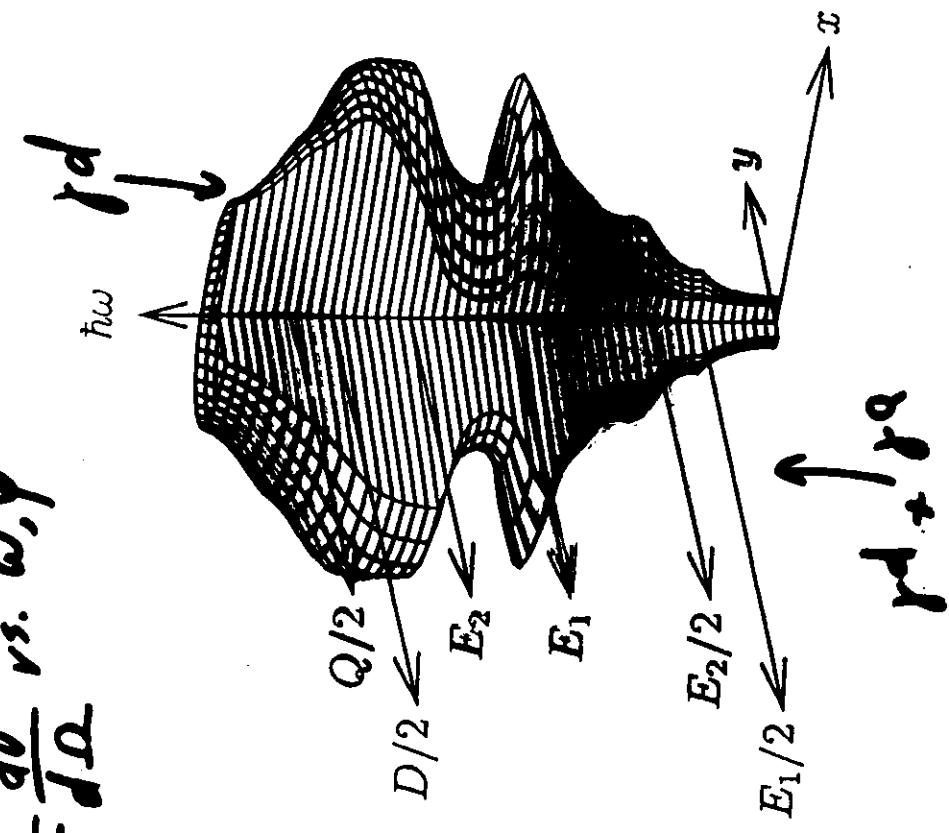


...large l

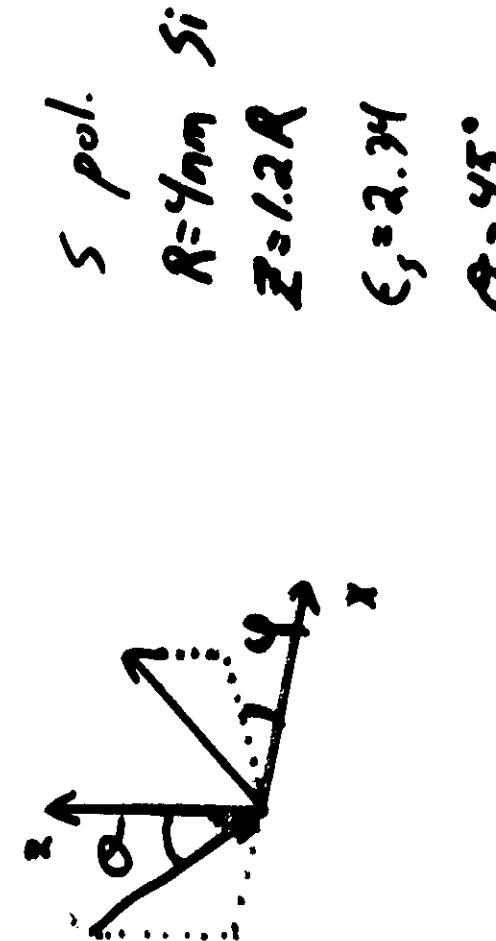


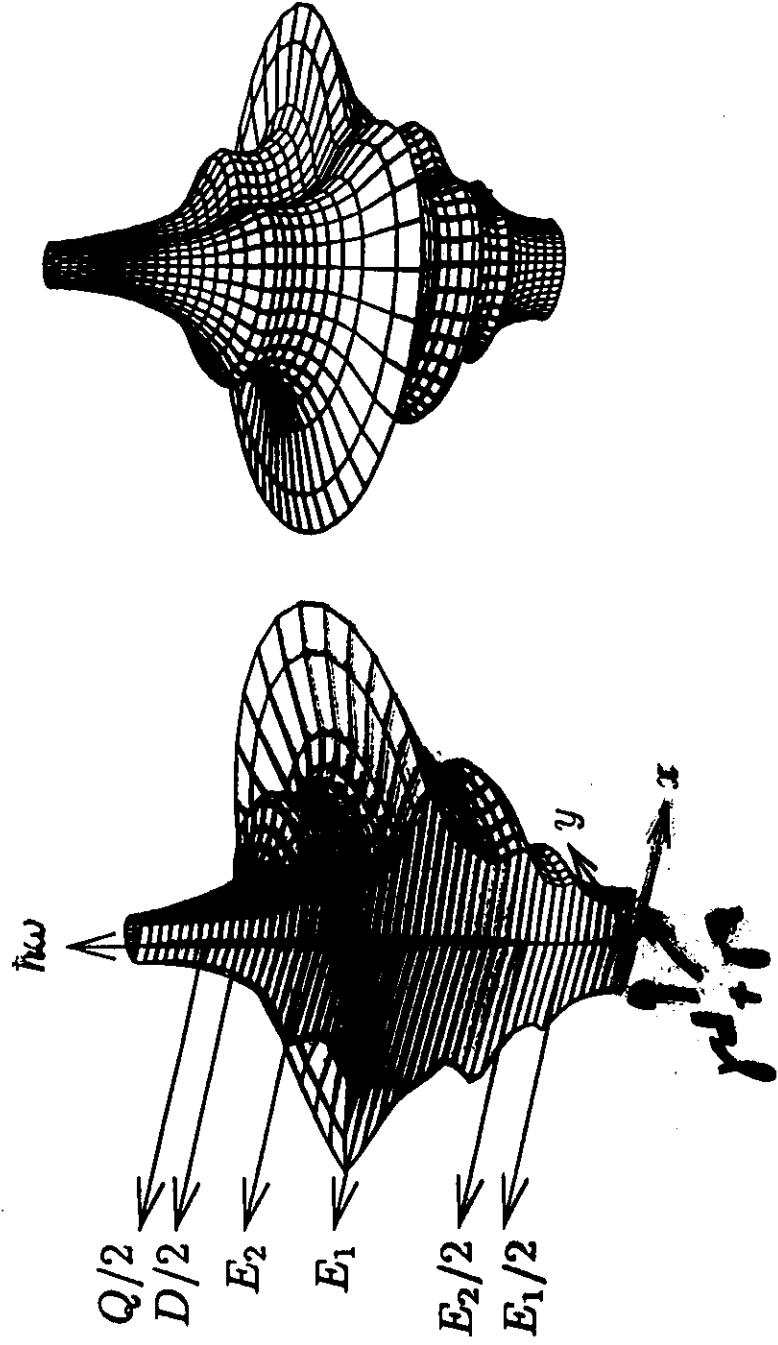


$$\frac{1}{\sqrt{\omega}} \frac{d\sigma}{d\Omega} \text{ vs. } \omega, \varphi$$



- Normalized SH efficiency ($d\sigma/d\Omega)/\omega^5$ scattered by a Si sphere of radius $R = 4$ μm illuminated with s polarized light at an angle of incidence $\theta = 45^\circ$ and of the incident photon energy $\hbar\omega$. We indicate the Cartesian axis, the dipolar D and quadrupolar Q resonances of the sphere.



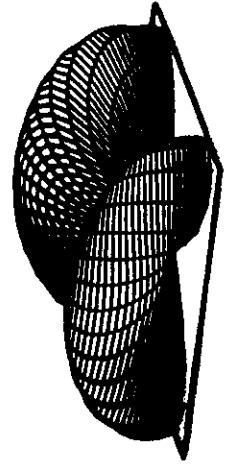
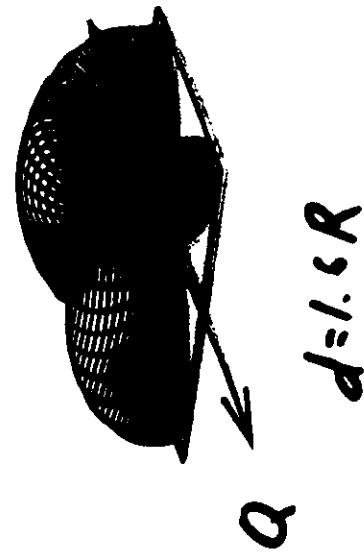
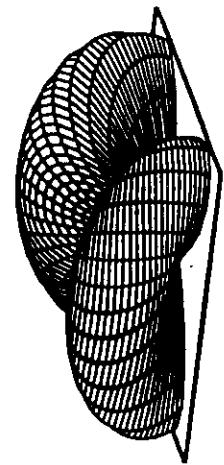
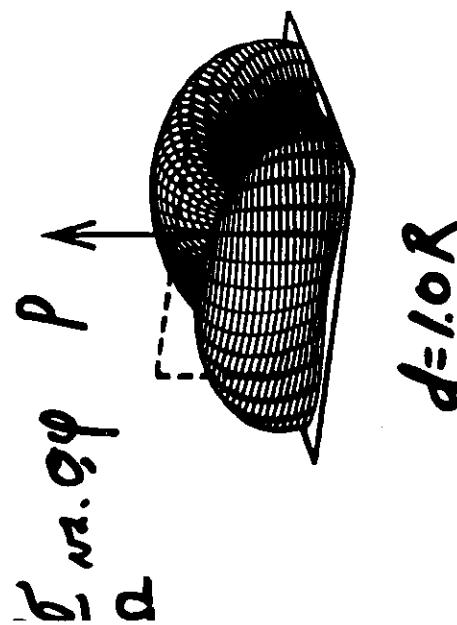


Normalized SH efficiency $(d\sigma/d\Omega)/\omega^5$ as in Fig. 8 (helado), but for p polarized at a distance $z = 1.4R$ over the substrate.

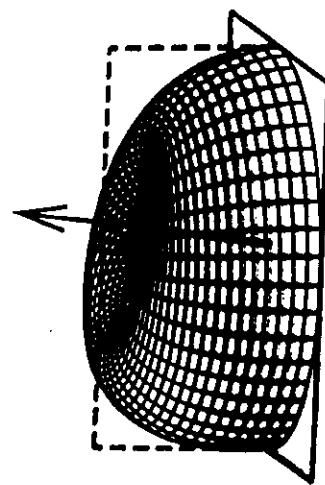
P. pol.

$$z = 1.4 R$$

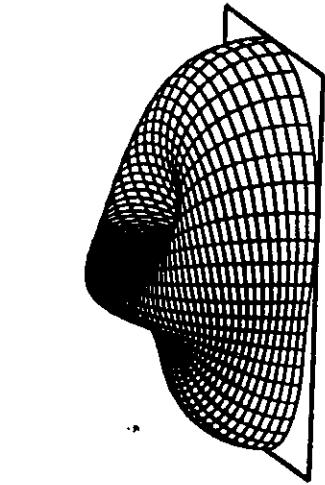
$$\hbar\omega = E_1$$



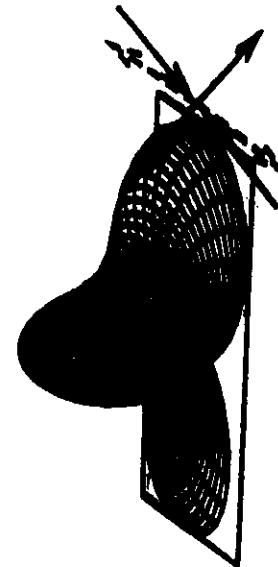
Efficiency $d\Omega/d\Omega$ of the SH radiation patterns produced by a 4nm Si nanosphere at several separation distances d , $1.0R$, $1.2R$, $1.4R$, and $1.6R$ (clockwise from upper left) over a dielectric substrate ($\epsilon' = 2.34$) illuminated by an excitation wave of energy $\hbar\omega = E_1$, as a function of the outgoing direction θ and φ . We indicate the plane of incidence (dashed rectangle), the direction of the induced dipole moment (single arrow), the induced quadrupolar moment (double headed arrow).



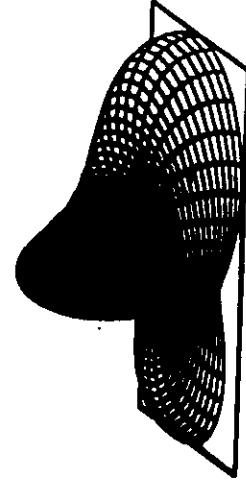
$$d = 1.0R$$



$$d = 1.4R$$



$$d = 1.6R$$



$$d = 1.8R$$

Efficiency $d\sigma/d\Omega$ of the SH radiation patterns produced by a 4nm Si nanosphere at $4R$, $1.6R$, and $1.8R$ (clockwise from upper left) over a dielectric substrate ($\epsilon_s = 2.34$) light of energy $\hbar\omega = E_1$, as a function of the outgoing direction θ and φ . We indicate the plane of incidence (dashed rectangle). For $d = R$ we show the direction normal (single headed arrow). For $d = 1.8R$ we show with double headed arrows the outgoing (solid) and normal to (dashed) the incidence plane. Their size indicates that of the \vec{Q} ; converging arrows correspond to nearly opposite phases than diverging arrows.

Conclusions

- Dipolium model for SHG of particles in inhomogeneous field.
- Analytical expressions for γ^d and γ^Q .
- $\gamma^\lambda \propto R^3/ne$ (bulk and surface).
- Comparable bulk and surface, dipole and quadrupole signals.
- Surface ($a(\omega)$) resonances and sphere resonances: dipolar_ω , $\text{dipolar}_{2\omega}$, and $\text{quadrupolar}_\omega$.
- $\sigma \approx (R/\lambda)^{6-\zeta} (R/\ell)^\zeta / (cn^2 e^2)$, $\zeta = 0 \dots 2$.
- p or Q (or none) dominate, depending on ℓ .

- Si spheres over a substrate, E_1 and E_2 , dipolar and quadrupolar resonances.
- Radiation pattern changes from dipolar to quadrupolar for $z \approx R \rightarrow 2R$. Asymmetric for p -polarization.